IXYS

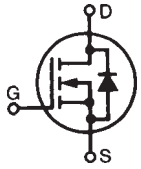
Preliminary Technical Information

Trench HiperFET™ Power MOSFET

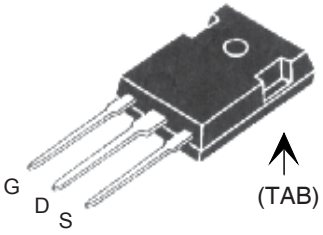
IXFH230N10T

V_{DSS} = 100V
I_{D25} = 230A
$R_{DS(on)}$ ≤ 4.7mΩ

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



TO-247



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 175°C	100	V
V_{DGR}	T_J = 25°C to 175°C, R_{GS} = 1MΩ	100	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	T_C = 25°C	230	A
I_{LRMS}	Lead Current Limit, RMS	160	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	500	A
I_A	T_C = 25°C	115	A
E_{AS}	T_C = 25°C	1.5	J
P_D	T_C = 25°C	650	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	1.6mm (0.062in.) from Case for 10s	300	°C
T_{sold}	Plastic Body for 10 Seconds	260	°C
Weight		6	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 1mA	100			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 1mA	2.5		4.5	V
I_{GSS}	V_{GS} = ± 20V, V_{DS} = 0V			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$			50	μA
	V_{GS} = 0V T_J = 150°C			3	mA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$ Notes 1, 2			4.7	mΩ

Features

- International Standard Package
- 175°C Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

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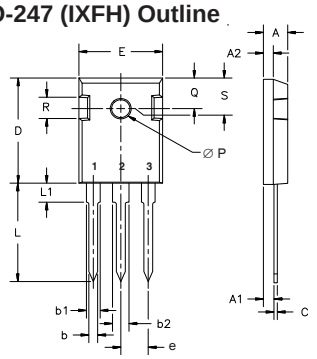
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10V, I_D = 60A, Note 1	80	135		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		15.3		nF
C_{oss}			1525		pF
C_{rss}			195		pF
$t_{d(on)}$	**Resistive Switching Times**		29		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 100A		40		ns
$t_{d(off)}$	R_G = 1Ω (External)		45		ns
t_f			15		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		250		nC
Q_{gs}			70		nC
Q_{gd}			65		nC
R_{thJC}				0.23	°C/W
R_{thCH}			0.21		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			230	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			900	A
V_{SD}	I_F = 100A, V_{GS} = 0V, Note 1			1.3	V
t_{rr}	I_F = 100A, V_{GS} = 0V		82		ns
I_{RM}	-di/dt = 100A/μs		4.8		A
Q_{RM}	V_R = 50V		196		nC

Note 1: Pulse Test, t ≤ 300μs; Duty Cycle, d ≤ 2%.

TO-247 (IXFH) Outline



Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ 25ºC

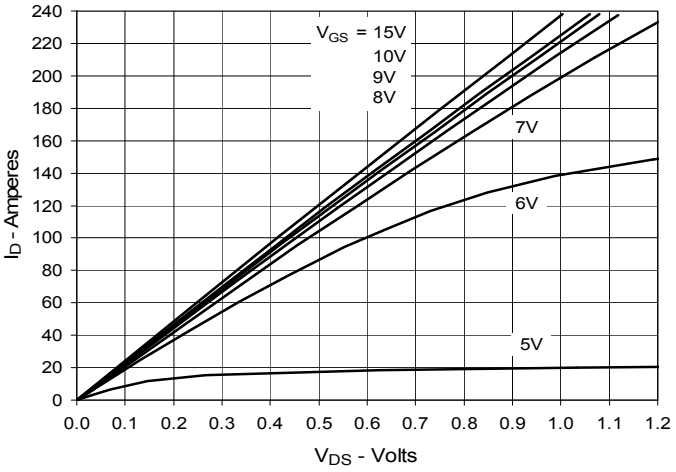


Fig. 2. Extended Output Characteristics @ 25ºC

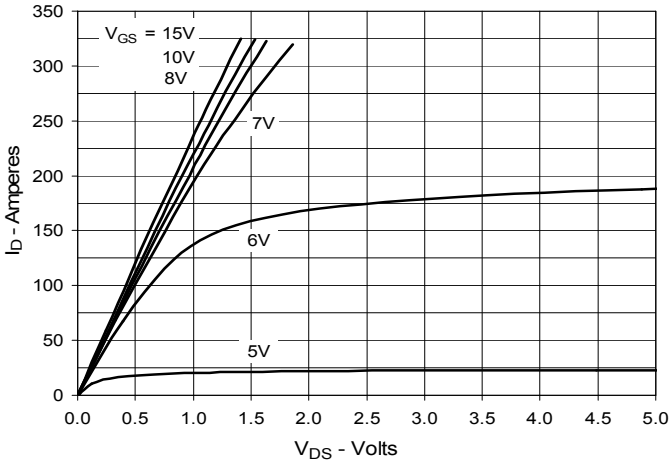


Fig. 3. Output Characteristics @ 150ºC

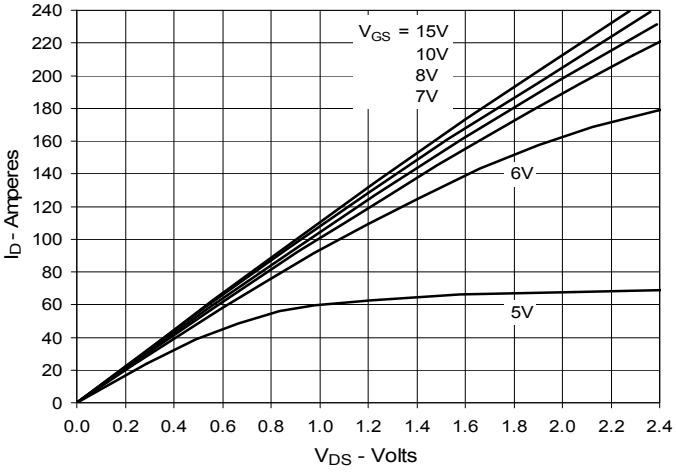


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 115A Value vs. Junction Temperature

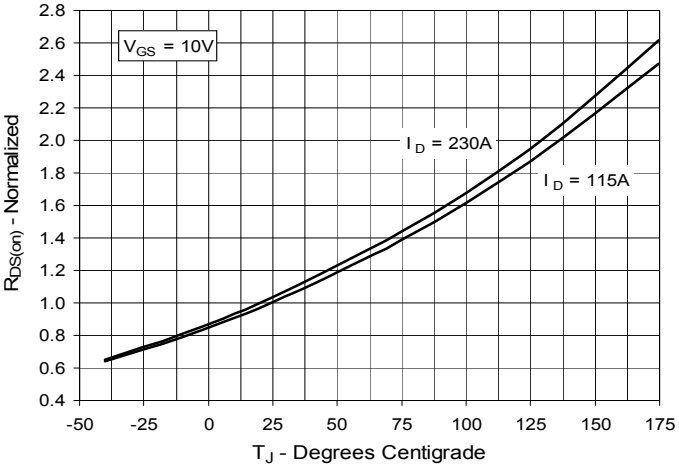


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 115A Value vs. Drain Current

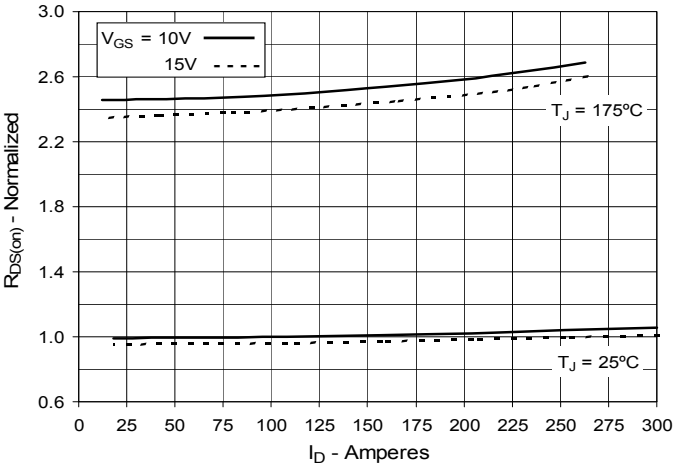
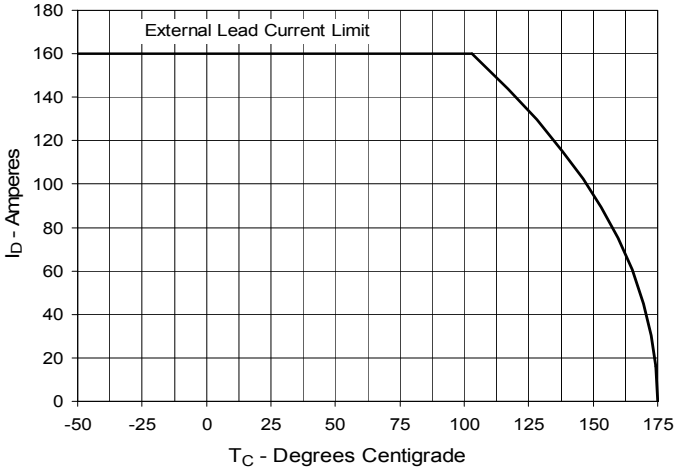


Fig. 6. Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

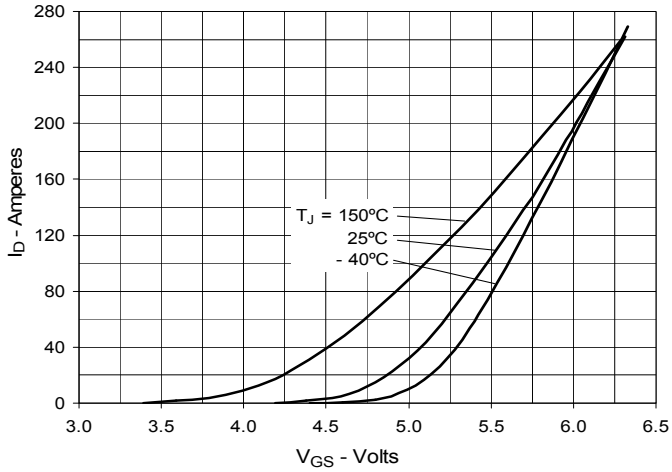


Fig. 8. Transconductance

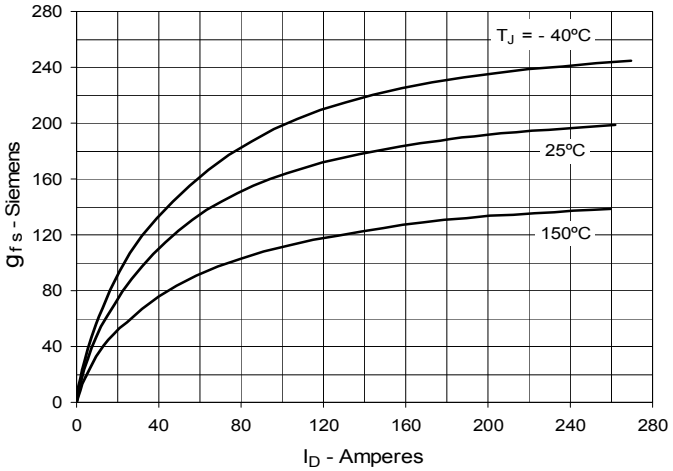


Fig. 9. Forward Voltage Drop of Intrinsic Diode

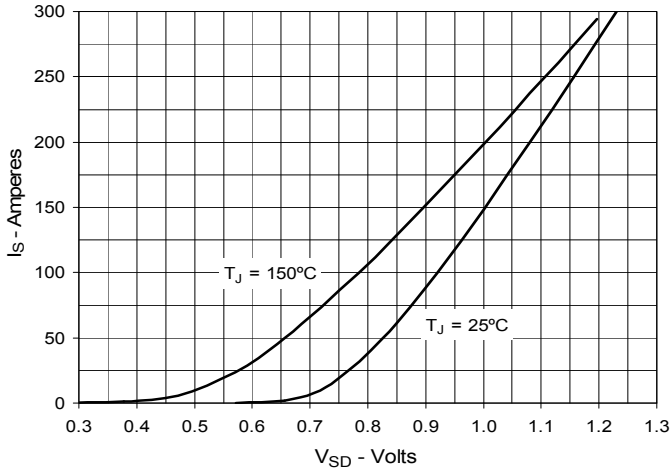


Fig. 10. Gate Charge

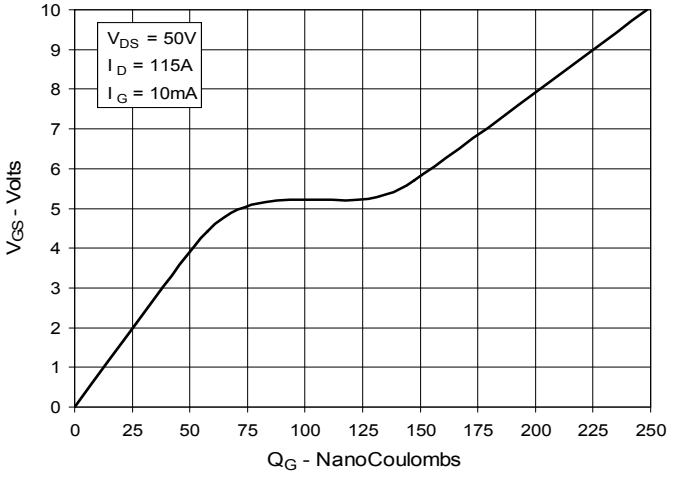


Fig. 11. Capacitance

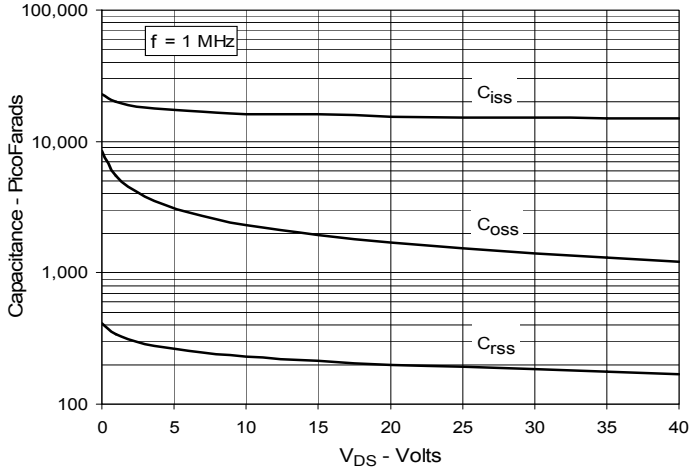
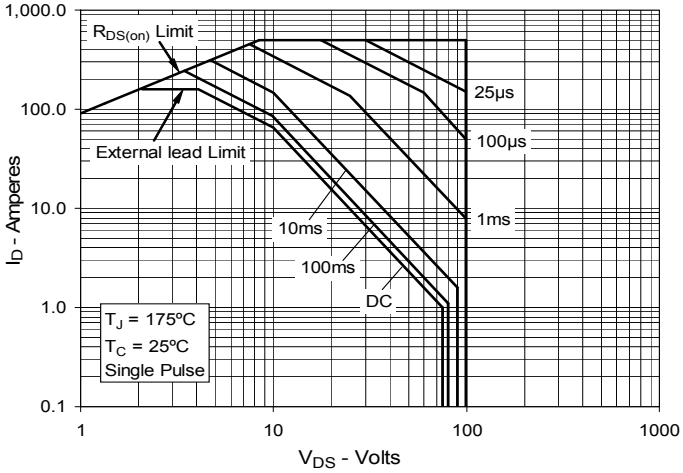


Fig. 12. Forward-Bias Safe Operating Area



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Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

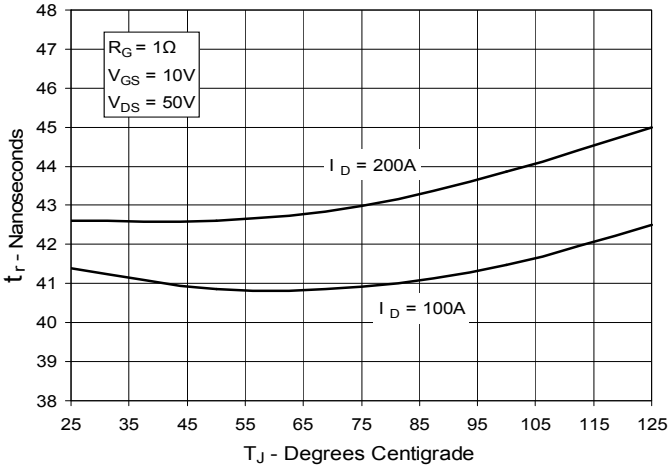


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

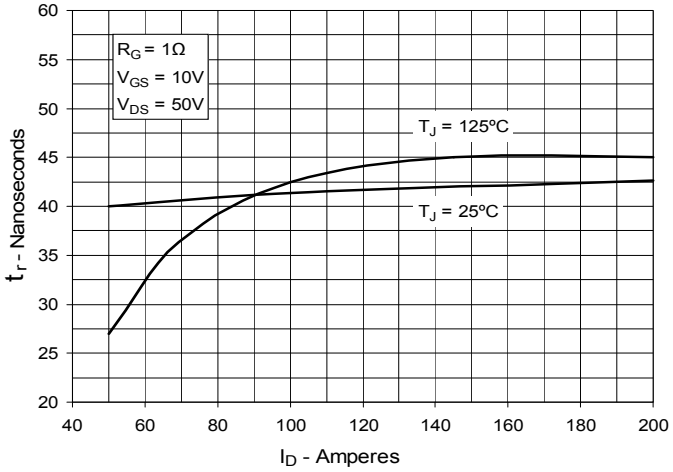


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

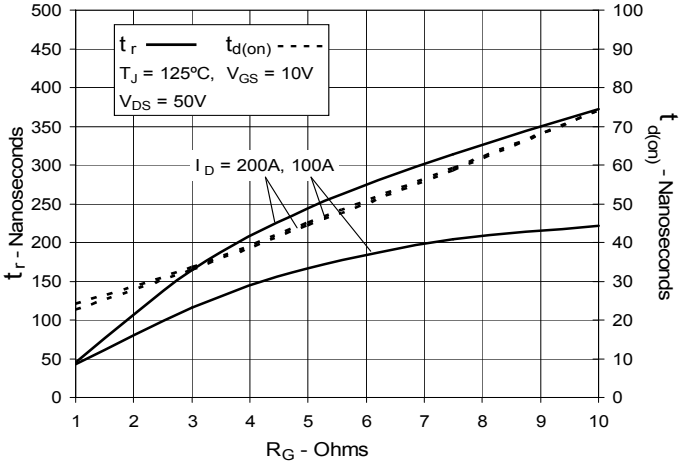


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

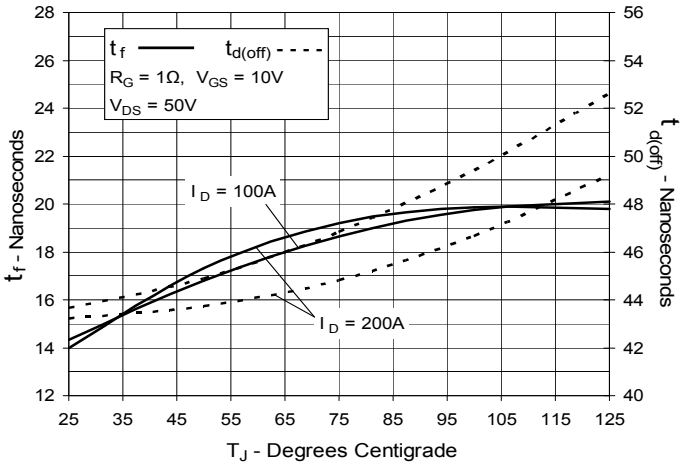


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

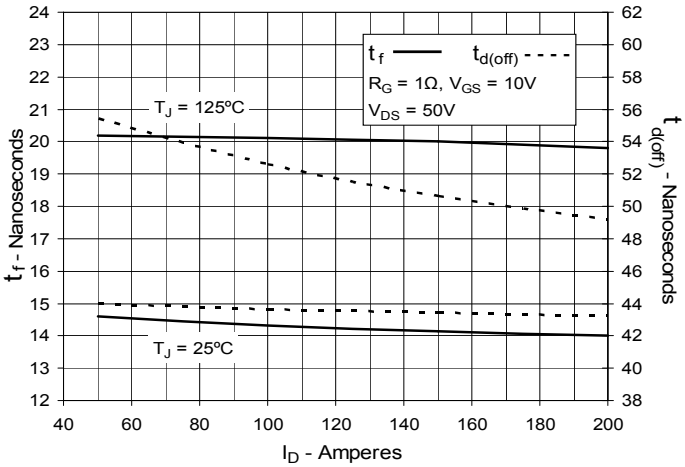
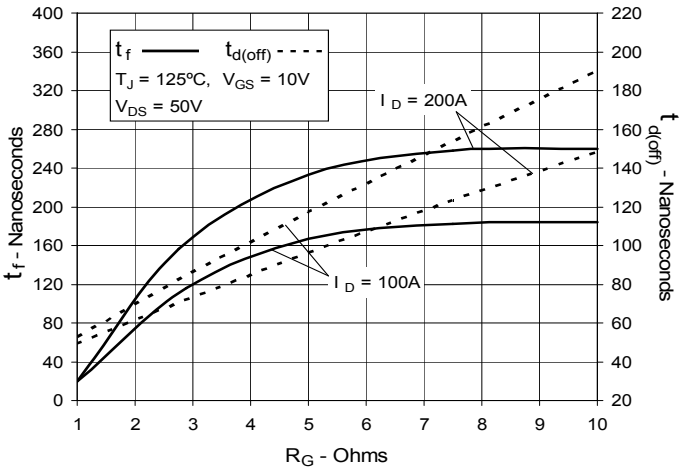
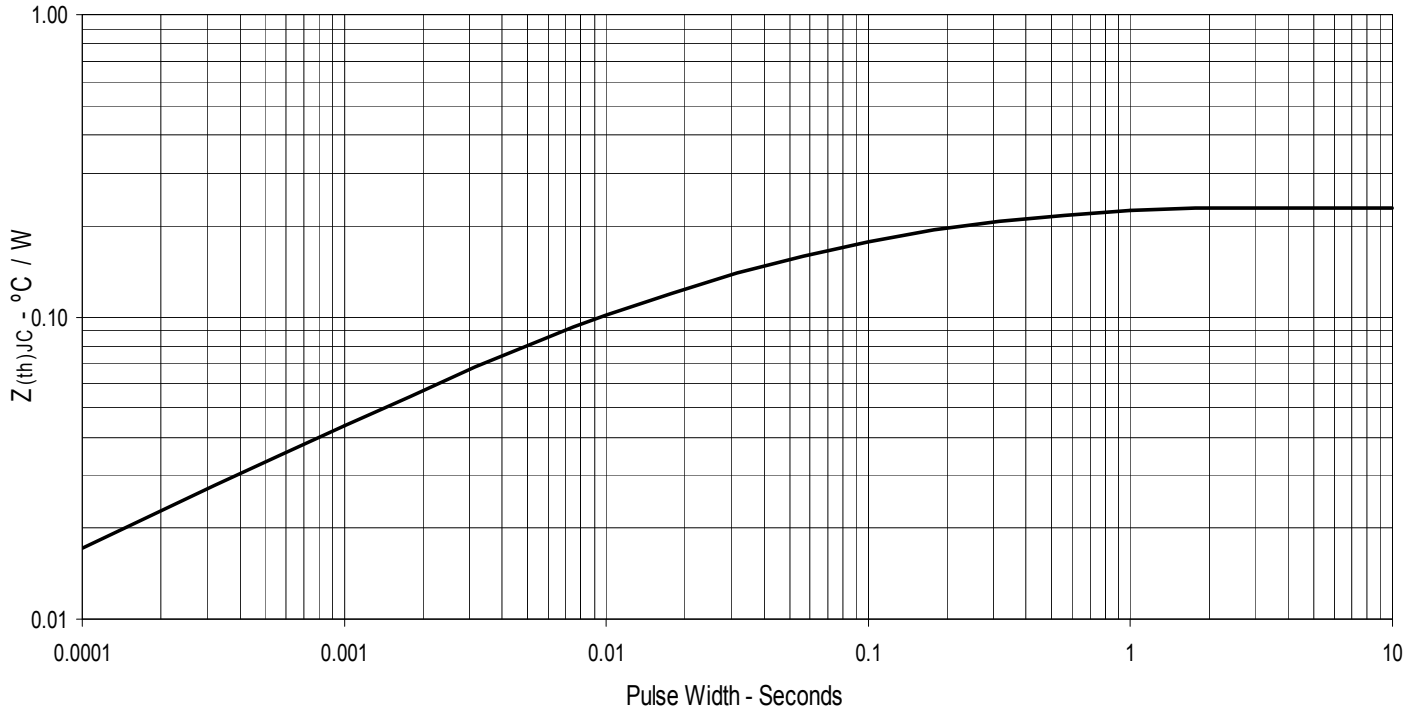


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance



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Fig. 19. Maximum Transient Thermal Impedance



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